

Product Overview

NSS30101L: Low $V_{CE(sat)}$ Transistor, NPN, 30 V, 2.0 A

For complete documentation, see the data sheet.

Low $V_{CE(sat)}$ Bipolar Transistors are miniature surface mount devices featuring ultra low saturation voltage $V_{CE(sat)}$ and high current gain capability. These are designed for use in low voltage, high speed switching applications where affordable efficient energy control is important.

Features

- High Current, Low V_{CEsat} , ESD Robust, High Current Gain, High Cut Off Frequency, Low Profile Package, Linear Gain (Beta)

Applications

- Load Switching, Battery Charging, External Pass Transistor, DC/DC Converter, Complimentary Driver, Current Extention & Low Drop Out Regulation, Cathode Florescent Lamp drive, Peripheral Driver - LEDs, Motors, Relays

Part Electrical Specifications

Product	Pricing (\$/Unit)	Compliance	Status	Polarity	Type	$V_{CE(sat) Max}$ (V)	I_C Cont. (A)	$V_{CEO Min}$ (V)	V_{CBO} (V)	V_{EBO} (V)	$V_{BE(sat)}$ (V)	$V_{BE(O)}$ (V)	$h_{FE Min}$	$h_{FE Max}$	f_T Min (MHz)	$P_{TM Max}$ (W)	Package Type
NSS30101LT1G	0.1073	Pb-free Halide free	Active	NPN	Low $V_{CE(sat)}$	0.2	1	30	50	5	1.1	1.1	300	900	100	0.71	SOT-23-3

For more information please contact your local sales support at www.onsemi.com.

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